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(54) **SEMICONDUCTOR STRUCTURE AND FORMING METHOD THEREOF**

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(57) **ABSTRACT**

A semiconductor structure and a method of forming it are disclosed by the present application. Deep trench capacitors are formed in a substrate, and fin contacts formed by upper portions of inner electrodes in the deep trench capacitors are connected to fins on a surface of the substrate. At least one of word lines formed on the substrate pass over and are separated by a word line isolation layer from the inner electrodes. The word line isolation layer covers portions of the inner electrodes between a buried oxide layer and the fin contacts, while the fins are exposed therefrom.